

SEMICONDUCTOR STRUCTURE AND METHOD OF FORMING THE SAME

Abstract of Disclosure

The present invention relates to a semiconductor structure and method of forming the same. The semiconductor structure includes a first substrate, a first adhesive/bonding stack on the surface of first substrate, wherein the first adhesive/bonding stack includes at least one first adhesive layer and at least one first bonding layer. The material of first bonding layer includes dielectrics such as silicon, nitrogen and carbon, the material of first adhesive layer includes dielectrics such as silicon and nitrogen, and the first adhesive/bonding stack of semiconductor structure is provided with higher bonding force in bonding process.

FIG. 2